

TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

# GT30J121

**High Power Switching Applications Fast Switching Applications** 

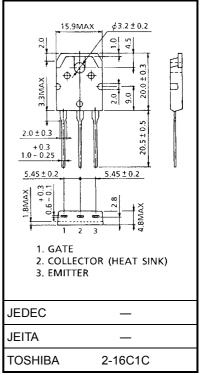
- The 4th generation •
- Enhancement-mode
- Fast switching (FS): Operating frequency up to 50 kHz (reference) High speed:  $t_f = 0.05 \ \mu s$  (typ.) Low switching loss:  $E_{on} = 1.00 \text{ mJ}$  (typ.)

 $: E_{off} = 0.80 \text{ mJ (typ.)}$ 

• Lo

Low saturation voltage: $V_{CE}$ (sat) = 2.0 V (typ.)								
aximum Ratings (1	Γa = 25°	C)						
Characteristics		Symbol	Rating	Unit				
Collector-emitter voltage		V <sub>CES</sub>	600	V				
Gate-emitter voltage		V <sub>GES</sub>	±20	V				
Collector current	DC	Ι <sub>C</sub>	30	٨				
	1 ms	I <sub>CP</sub>	60	A				
Collector power dissipation (Tc = 25°C)		P <sub>C</sub>	170	W				
Junction temperature		Тj	150	°C				
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C				

#### Max



Weight: 4.6 g (typ.)

### **Thermal Characteristics**

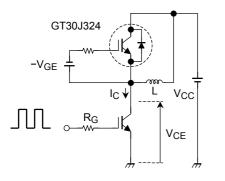
Characteristics	Symbol	Max	Unit
Thermal resistance	R <sub>th (j-c)</sub>	0.735	°C/W

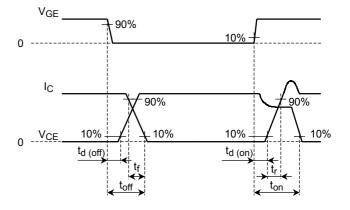
Unit: mm

Electrical Characteristics (Ta = 25°C)

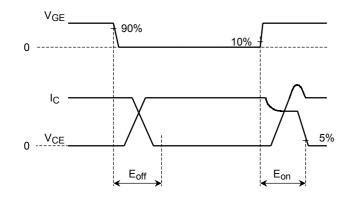
Cha	racteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	urrent	I <sub>GES</sub>	$V_{GE}$ = ±20 V, $V_{CE}$ = 0		_	±500	nA
Collector cut-off	current	ICES	V <sub>CE</sub> = 600 V, V <sub>GE</sub> = 0		_	1.0	mA
Gate-emitter cur	t-off voltage	V <sub>GE (OFF)</sub>	$I_C$ = 3 mA, $V_{CE}$ = 5 V	3.5	—	6.5	V
Collector-emitte	r saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 30 A, V <sub>GE</sub> = 15 V	_	2.0	2.45	V
Input capacitance		Cies	$V_{CE}$ = 10 V, $V_{GE}$ = 0, f = 1 MHz	_	4650	—	pF
Switching time	Turn-on delay time	t <sub>d (on)</sub>	Inductive Load $V_{CC} = 300 \text{ V}, \text{ I}_{C} = 30 \text{ A}$ $V_{GG} = +15 \text{ V}, \text{ R}_{G} = 24 \Omega$ (Note 1) (Note 2)	_	0.09	—	μs ·
	Rise time	tr		_	0.07	_	
	Turn-on time	t <sub>on</sub>			0.24	_	
	Turn-off delay time	t <sub>d (off)</sub>		_	0.30	_	
	Fall time	t <sub>f</sub>		_	0.05	_	
	Turn-off time	t <sub>off</sub>		_	0.43	_	
Switching loss	Turn-on switching loss	E <sub>on</sub>		_	1.00	_	mJ
	Turn-off switching loss	E <sub>off</sub>		—	0.80	—	

Note 1: Switching time measurement circuit and input/output waveforms

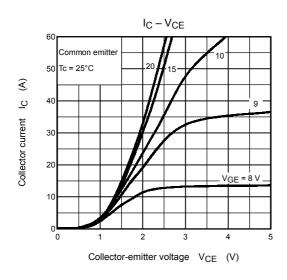


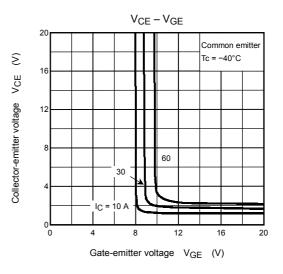


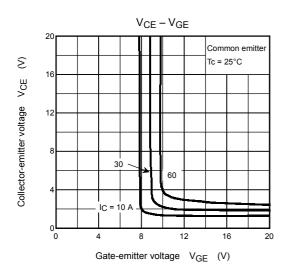
#### Note 2: Switching loss measurement waveforms

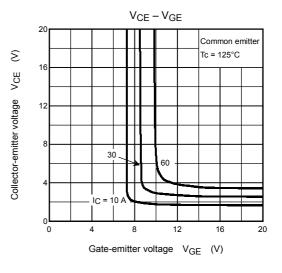


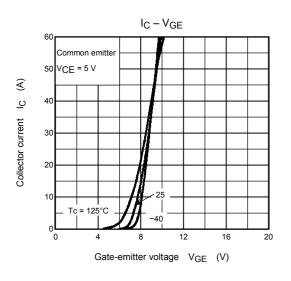
## **TOSHIBA**

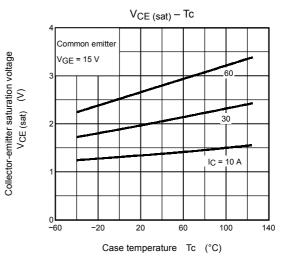




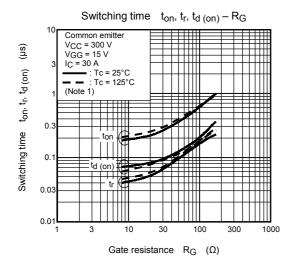


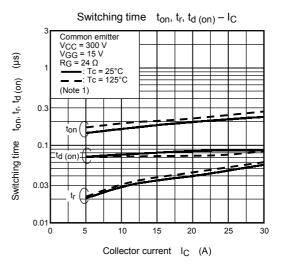




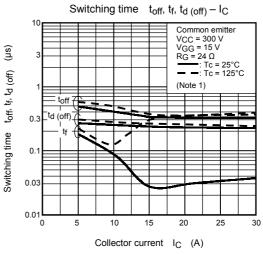


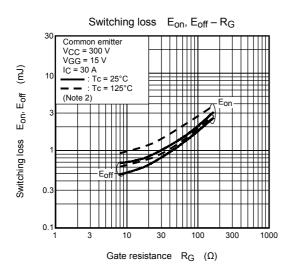
### TOSHIBA

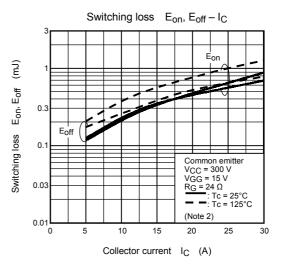




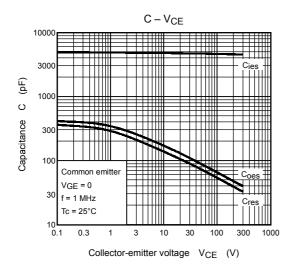
Switching time  $t_{off}, t_{f}, t_{d (off)} - R_G$ 10 Common emitter  $V_{CC} = 300 V$   $V_{GG} = 15 V$   $I_{C} = 30 A$   $\therefore T_{C} = 25^{\circ}C$   $\therefore T_{C} = 125^{\circ}C$ (srl) 3 toff, tf, td (off) (Note 1) 0.3 toff d (off ŧ Switching time 0.1 +## 0.03 tf 0.01 300 3 30 1000 10 100 Gate resistance  $R_G$  ( $\Omega$ )

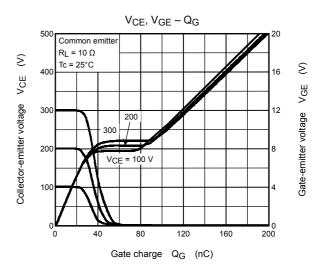




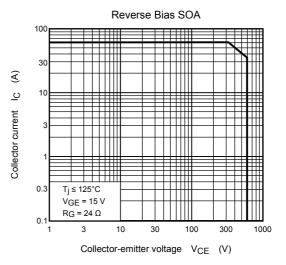


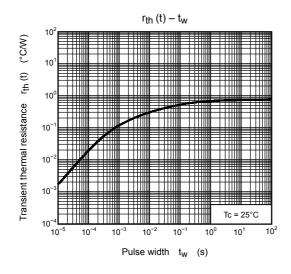
### **TOSHIBA**





Safe Operating Area 100 IC max (pulsed)\* IC max (continuous) 30 100 € 10 <u>ں</u> DC operation Collector current Single pulse  $Tc = 25^{\circ}C$ Curves must be derated linearly 0.3 with increase in temperature. 0.1 3 10 30 300 1000 100 Collector-emitter voltage V<sub>CE</sub> (V)





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